

## 2SK2408

### Silicon N Channel MOS FET

REJ03G1011-0300  
(Previous: ADE-208-1358)  
Rev.3.00  
Apr 27, 2006

#### Application

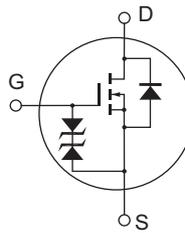
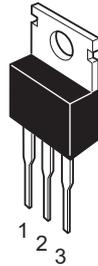
High speed power switching

#### Features

- Low on-resistance
- Built-in fast recovery diode ( $t_{rr} = 120$  ns typ)
- High speed switching
- Low drive current
- Suitable for switching regulator, motor control

#### Outline

RENESAS Package code: PRSS0004AC-A  
(Package name: TO-220AB)



1. Gate
2. Drain  
(Flange)
3. Source

## Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	500	V
Gate to source voltage	$V_{GSS}$	±30	V
Drain current	$I_D$	7	A
Drain peak current	$I_{D(pulse)}^{*1}$	28	A
Body to drain diode reverse drain current	$I_{DR}$	7	A
Channel dissipation	$P_{ch}^{*2}$	60	W
Channel temperature	$T_{ch}$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

Notes: 1.  $PW \leq 10 \mu s$ , duty cycle  $\leq 1 \%$   
 2. Value at  $T_c = 25^\circ C$

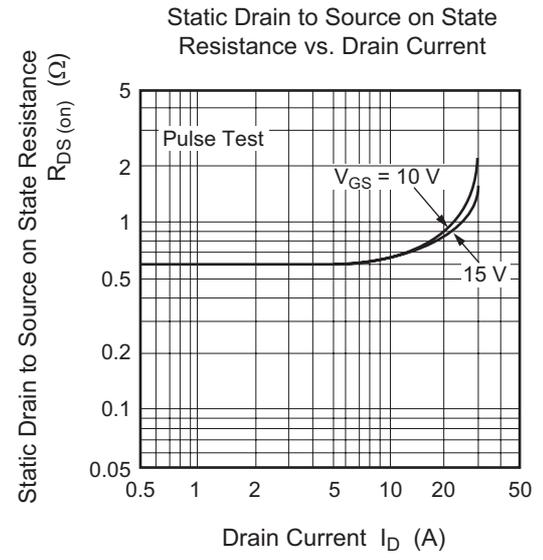
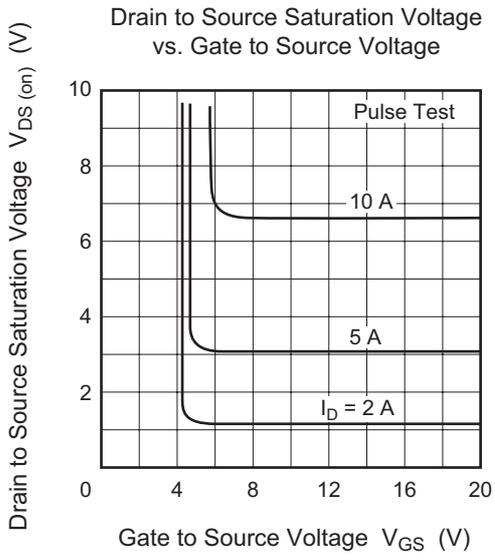
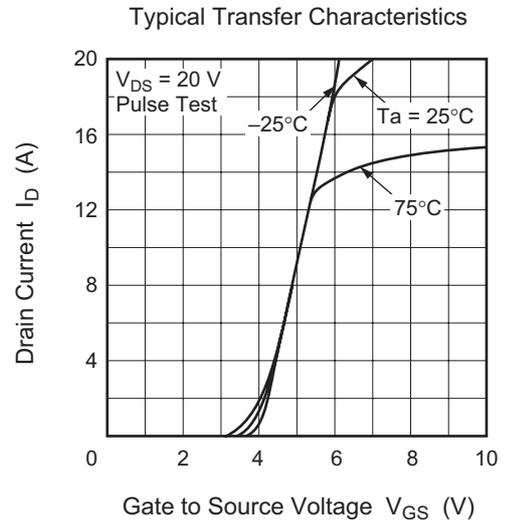
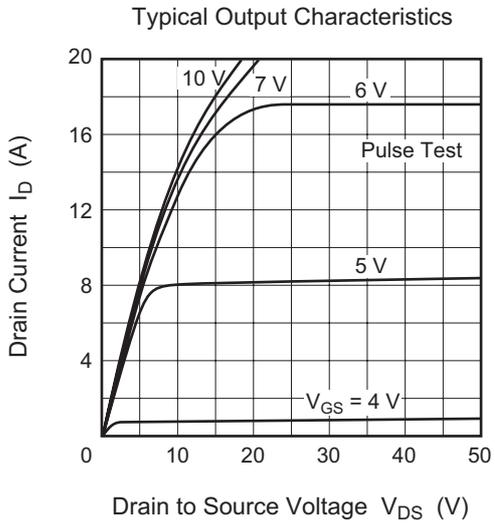
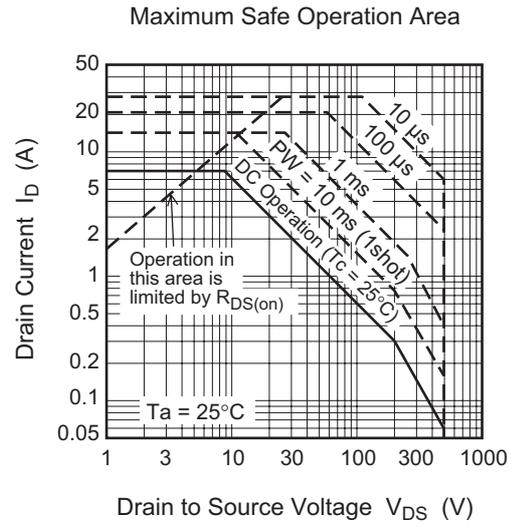
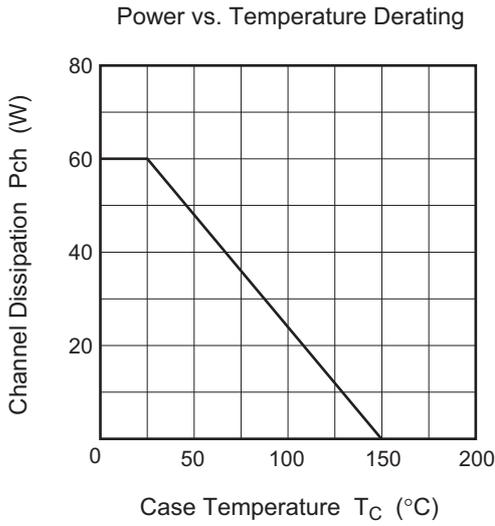
## Electrical Characteristics

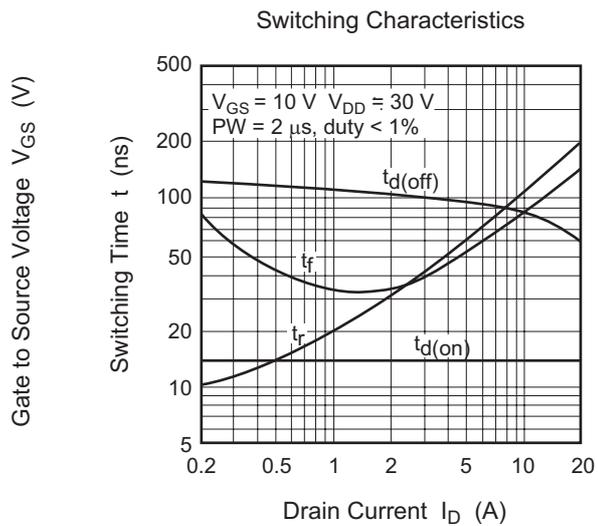
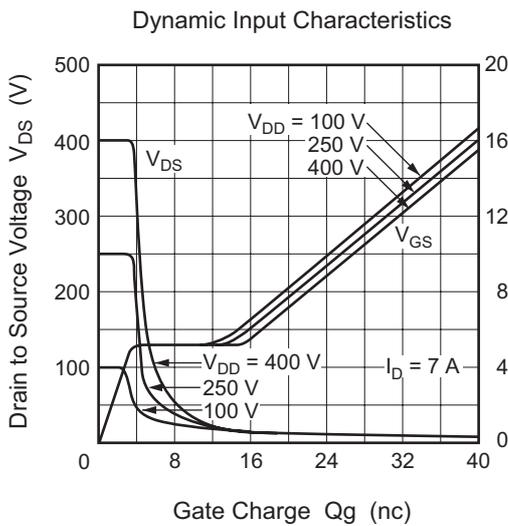
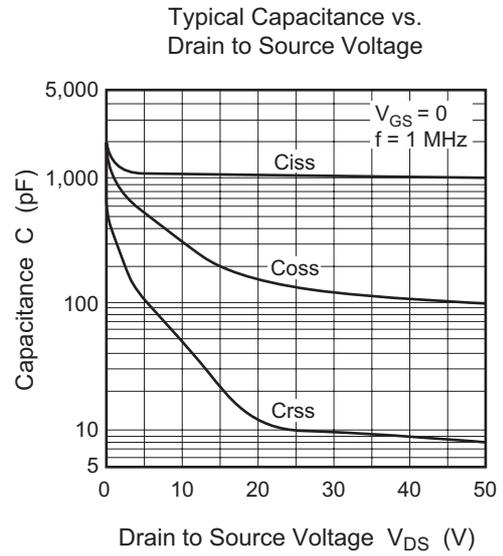
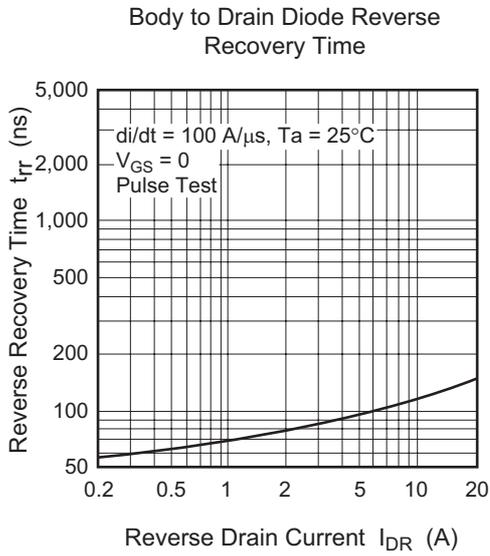
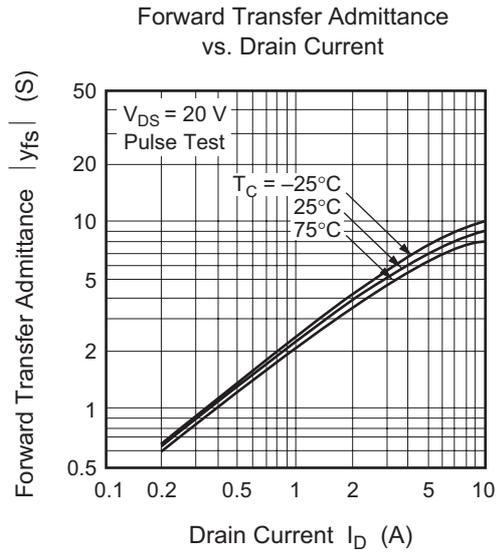
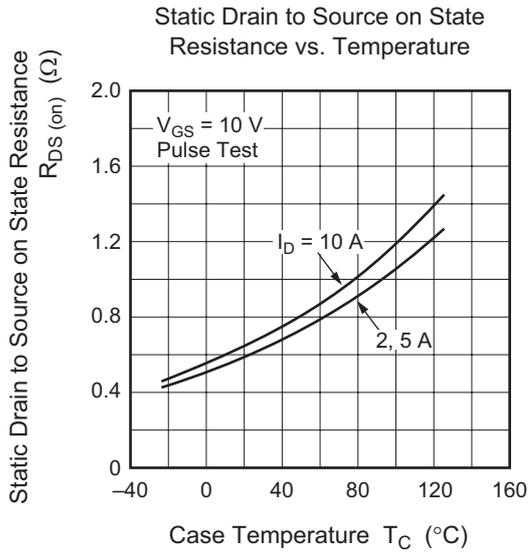
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	500	—	—	V	$I_D = 10 \text{ mA}$ , $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±30	—	—	V	$I_G = \pm 100 \mu A$ , $V_{DS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	±10	μA	$V_{GS} = \pm 25 \text{ V}$ , $V_{DS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	250	μA	$V_{DS} = 400 \text{ V}$ , $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	—	3.0	V	$I_D = 1 \text{ mA}$ , $V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.7	0.9	Ω	$I_D = 4 \text{ A}$ , $V_{GS} = 10 \text{ V}^{*3}$
Forward transfer admittance	$ y_{fs} $	3.5	6.0	—	S	$I_D = 4 \text{ A}$ , $V_{DS} = 10 \text{ V}^{*3}$
Input capacitance	$C_{iss}$	—	1100	—	pF	$V_{DS} = 10 \text{ V}$ , $V_{GS} = 0$ , $f = 1 \text{ MHz}$
Output capacitance	$C_{oss}$	—	310	—	pF	
Reverse transfer capacitance	$C_{rss}$	—	50	—	pF	
Turn-on delay time	$t_{d(on)}$	—	15	—	ns	$I_D = 4 \text{ A}$ , $V_{GS} = 10 \text{ V}$ , $R_L = 7.5 \Omega$
Rise time	$t_r$	—	55	—	ns	
Turn-off delay time	$t_{d(off)}$	—	100	—	ns	
Fall time	$t_f$	—	48	—	ns	
Body to drain diode forward voltage	$V_{DF}$	—	0.9	—	V	$I_F = 7 \text{ A}$ , $V_{GS} = 0$
Body to drain diode reverse recovery time	$t_{rr}$	—	120	—	ns	$I_F = 7 \text{ A}$ , $V_{GS} = 0$ , $di_F / dt = 100 \text{ A} / \mu s$

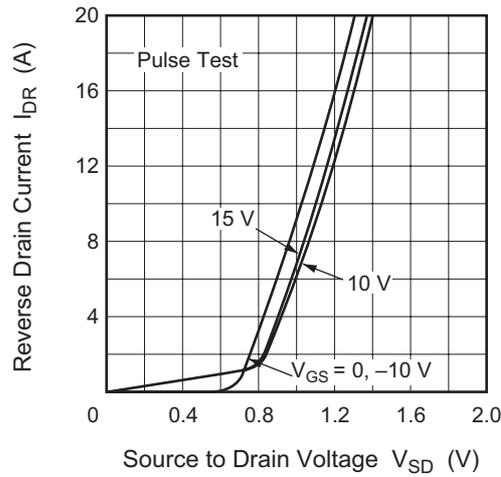
Note: 3. Pulse Test

Main Characteristics

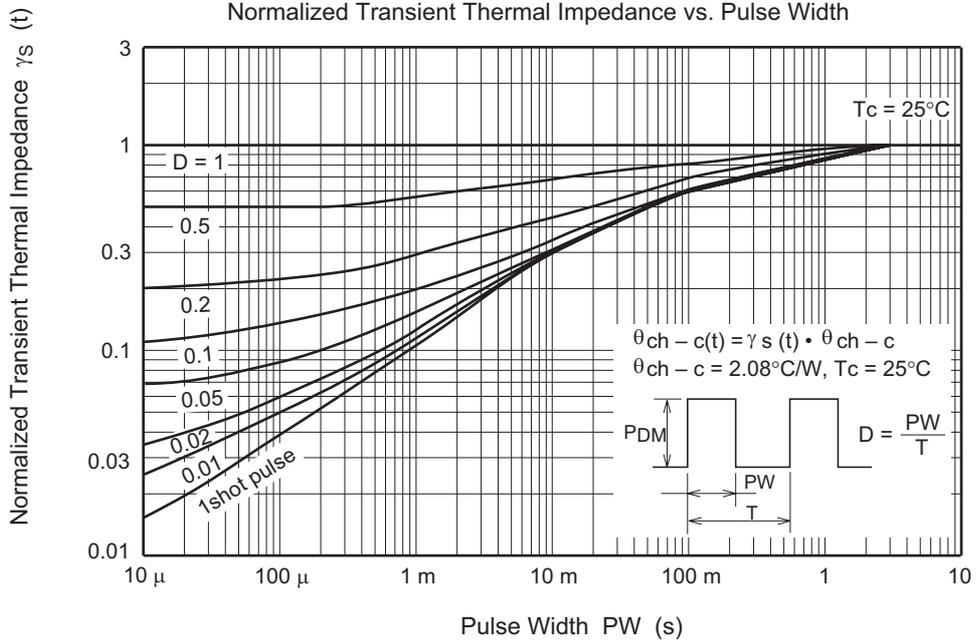




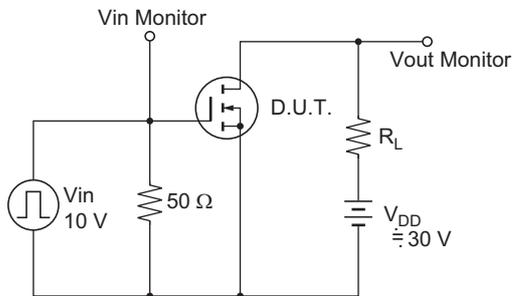
Reverse Drain Current vs. Source to Drain Voltage



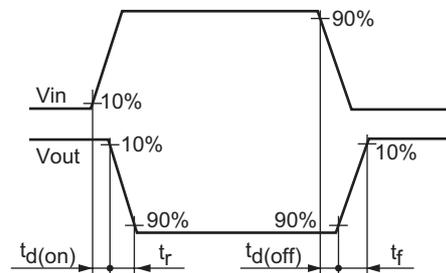
Normalized Transient Thermal Impedance vs. Pulse Width



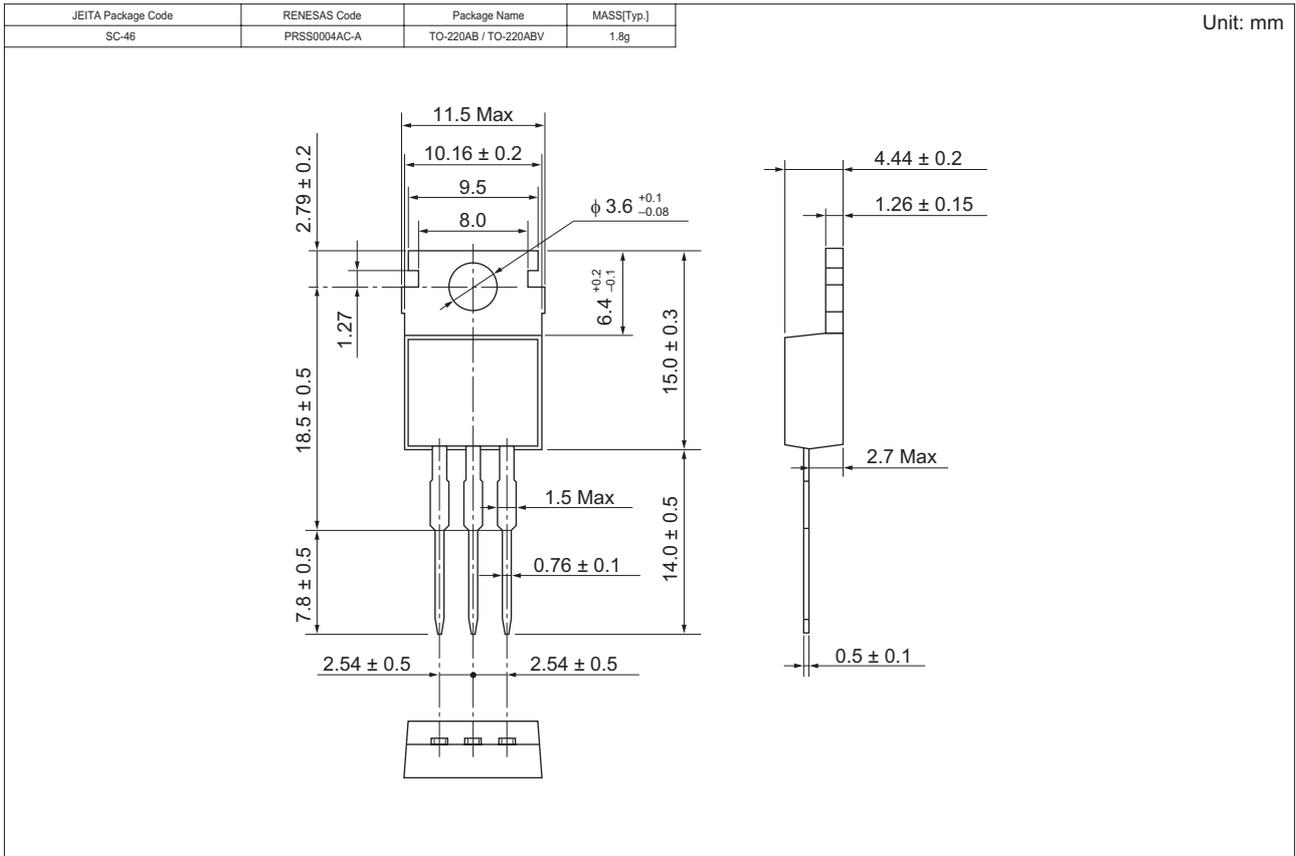
Switching Time Test Circuit



Waveforms



### Package Dimensions



### Ordering Information

Part Name	Quantity	Shipping Container
2SK2408-E	500 pcs	Box (Sack)

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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**Renesas Technology America, Inc.**

450 Holger Way, San Jose, CA 95134-1368, U.S.A  
Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

**Renesas Technology Europe Limited**

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.  
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

**Renesas Technology (Shanghai) Co., Ltd.**

Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120  
Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7898

**Renesas Technology Hong Kong Ltd.**

7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong  
Tel: <852> 2265-6688, Fax: <852> 2730-6071

**Renesas Technology Taiwan Co., Ltd.**

10th Floor, No.99, Fushing North Road, Taipei, Taiwan  
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

**Renesas Technology Singapore Pte. Ltd.**

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632  
Tel: <65> 6213-0200, Fax: <65> 6278-8001

**Renesas Technology Korea Co., Ltd.**

Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea  
Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

**Renesas Technology Malaysia Sdn. Bhd**

Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia  
Tel: <603> 7955-9390, Fax: <603> 7955-9510